

isc Silicon NPN Power Transistor

BUX24

DESCRIPTION

- Low Collector Saturation Voltage-
- High Switching Speed
- · High Current Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

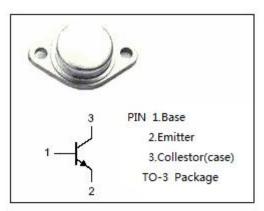
• Desinged for use in switching and linear applications in military and industrial equipment.

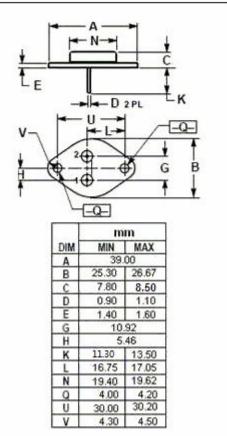


| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------|
| V _{CBO} | Collector-Base Voltage | 450 | V |
| V _{CEO} | Collector-Emitter Voltage | 400 | V |
| VEBO | Emitter-Base Voltage | 7 | V |
| lc | Collector Current-Continuous | 20 | А |
| Ісм | Collector Current-Peak | 30 | А |
| I _B | Base Current-Continuous | 4 | А |
| Pc | Collector Power Dissipation @Tc=25°C | 350 | W |
| Tj | Junction Temperature | 200 | °C |
| T _{stg} | Storage Temperature Range | -65~200 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|---------------------|--------------------------------------|-----|-------------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.5 | ℃ /W |







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ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|-------------------------|--------------------------------------|---|-----|------|-------------|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 50mA; I _B = 0 | 400 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 7 | | | V |
| V _{CE} (sat)-1 | Collector-Emitter Saturation Voltage | I _C = 6A; I _B = 1.2A | | | 0.6 | V |
| V _{CE(sat)} -2 | Collector-Emitter Saturation Voltage | I _C = 12A ;I _B = 2.4A | | | 1.0 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C = 12A ;I _B = 2.4A | | | 1.5 | V |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 320V; I _B = 0 | | | 3.0 | mA |
| I _{CBO} | Collector Cutoff Current | V_{CB} = 450V; I _E = 0 V_{CB} =450V; I _E = 0;T _C =125°C | | | 3.0 12.0 | mA |
| І _{ЕВО} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 1.0 | mA |
| h _{FE-1} | DC Current Gain | I _C = 6A ; V _{CE} = 4V | 15 | | 60 | |
| h _{FE-2} | DC Current Gain | I _C = 12A ; V _{CE} = 4V | 8 | | | |
| fT | Current-Gain—Bandwidth Product | I _C = 2A; V _{CE} = 15V, f _{test} = 10MHz | 8 | | | MHz |

NOTICE:

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